

Form PTO-1449 (Modified)		AMAT Atty Docket No.: 005794 ALRT/ETCH/CONE BSTZ Docket No.: 4887P578		Serial No.: Not Yet Assigned	
List of Patents and Publications Statement (Use several sheets if necessary)			Applicant: Kawaguchi, et al.		
Page 1 of 3			Filing Date: Herewith		

J-857 U.S. PTO
 09/978121

 10/15/01

U.S. PATENT DOCUMENTS						
Examiner Initials	Document No.	Document No.	Inventor	Class	Sub-Class	Filing date if appropriate
<i>And</i>	AA	6,007,671	Fujimura, et al.	156	345	8/20/1996
	AB	5,403,436	Fujimura, et al.	156	643	7/11/1994
	AC	6,024,045	Kikuchi, et al.	118	723 ME	10/26/1998
	AD	5,773,201	Fujimura, et al.	430	329	2/9/1994
	AE	4,431,898	Reinberg, et al.	219	121 PG	9/1/1981
	AF	5,174,856	Hwang, et al.	156	643	8/26/1991
	AG	5,200,031	Latchford, et al.	156	659.1	8/26/1991
	AH	5,221,424	Rhoades	156	643	11/21/1991
	AI	5,545,289	Chen, et al.	156	643.1	6/29/1994
	<i>And</i>	AJ	6,150,628	Smith, et al.	219	121.54
AK						

FOREIGN PATENT DOCUMENTS							
No.	Document No.	Date	Country	Class	Sub-Class	Trans-lation	
<i>And</i>	AL	WO 01/11650 A1	2/15/2001	PCT	A1		
	AM						
	AN						
	AO						
	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>And</i>	AR	Kikuchi, et al., "Effects of H ₂ O on Atomic Hydrogen Generation in Hydrogen Plasma," June 1993, Jpn. J. Appl Phys. Vol. 32 (1993) Part 1, No. 6B, pp. 3120-3124.
<i>And</i>	AS	Chang, et al., "Suppression of Copper Diffusion Through Barrier Metal-Free Hydrogen Silsesquioxane Dielectrics by NH ₃ Plasma Treatment," June 2, 1999, Electrochemical and Solid State Letters, pp 634-636.
<i>And</i>	AT	Nakagawa, et al., "RIE-Lag-Less Etching by CH ₄ /N ₂ Plasma for Organic Low-k Dielectric," 2000, 2000 Dry Process Symposium, ULSI Process Technology Development Center, Semiconductor Company, Matsushita Electronics Corp., Institute for Semiconductor Technologies, ULVAC Japan Ltd., pp. 257-262.

Examiner <i>Allen Olson</i>	Date Considered <i>6.24.03</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	AI						
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	AN						
	AO						
	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AR	Morikawa, et al., "Organic Low-k Etching Process in Low Pressure and High Density NLD Plasma", 2000, 2000 Dry Process Symposium, pp. 263-268.
	AS	Janowiak, et al., "Etching of organic low dielectric constant material SiLK TM on the Lam Research Corporation 4520XLE TM ," J. Vac. Sci. Technol., Jul/Aug 2000, 2000 American Vacuum Society, pp. 1859-1863.
	AT	Chang, et al., "The Novel Improvement of Low Dielectric Constant Methylsilsesquioxane by N ₂ O Plasma Treatment," Journal of The Electrochemical Society, October 20, 1998, pp. 3802-3806.
Examiner		Date Considered 6-27-03

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Form PTO-1449 (Modified)	AMAT Atty Docket No.: 005794 ALRT/ETCH/CONE BSTZ Docket No.: 4887P578	Serial No.: Not Yet Assigned
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	AM						
	AN						
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	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>AR</i>	AR	Louis, et al., "Improved Post Etch Cleaning for low-k and copper integration for 0.18 μ m Technology," <i>Microelectronic Engineering</i> 46 (1999), pp. 307-310.
<i>AS</i>	AS	Kikuchi, et al., "Native Oxide Removal on Si Surfaces by NF ₃ -Added Hydrogen and Water Vapor Plasma Downstream Treatment," <i>Jpn. J. Appl. Phys. Vol. 33 (1994), Part 1, No. 4B, April 1994, pp. 2207-2211.</i>
<i>AT</i>	AT	Kikuchi, et al., "Cleaning of Silicon Surfaces by NF ₃ - Added Hydrogen and Water-Vapor Plasma Downstream Treatment," <i>Jpn J. Appl. Phys. Vol. 35 (1996), Part 1, No. 2B, February 1996, pp. 1022-1026.</i>

Examiner <i>Allen Olson</i>	Date Considered <i>6.24.03</i>
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Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)

Complete if Known

Application Number	09/978,121
Filing Date	10/15/2001
First Named Inventor:	Kawaguchi
Art Unit	1733
Examiner Name	Unassigned
Attorney Docket Number	005794
	ALRT/ETCH/CONE/

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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (If known)				
Aco Aco		US-	6,235,453 B1	05-22-2001	You, et al.	
		US-	2001/0024769 A1	09-27-2001	Donoghue, et al.	
		US-				
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
Aco			EP 0 463 870 A1		01-02-1992	Fujitsu Limited/Fujimura, et al.		

Examiner Signature	<i>[Signature]</i>	Date Considered	6-19-03
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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia, 22313-1450.

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